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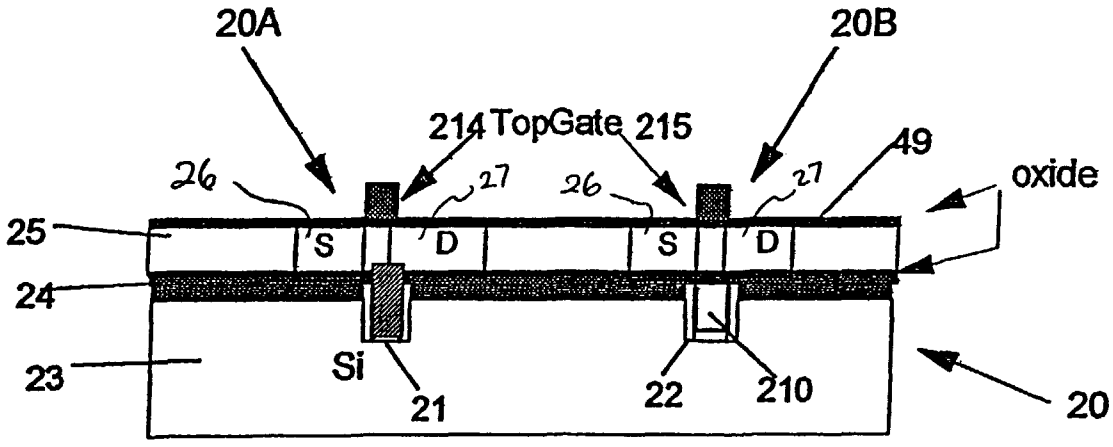
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(54) Title: METHOD AND STRUCTURE FOR BURIED CIRCUITS AND DEVICES



(57) Abstract: A method and structure for fabricating an electronic device (20A) using an SOI technique that results in formation of a buried oxide layer (24). The method includes fabricating at least one first component (21,22) of the electronic device in a first single crystal semiconductor layer (23), and fabricating at least one second component (26,27) of the electronic device in a second single crystal semiconductor layer (25) separated from the first single crystal semiconductor layer (23) by a buried oxide layer (24), wherein the buried oxide layer (24) is modified locally to perform a fonction integral to the electronic device (20A). Entire circuits can be designed using this technique.

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